



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors





Z0107NA

4Q Triac

6 May 2015

Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

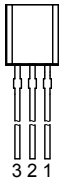
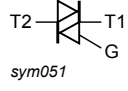
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{J(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$	-	-	8	A
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 45\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	5	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	-	7	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 <p>TO-92 (SOT54)</p>	 <p>sym051</p>
2	G	gate		
3	T1	main terminal 1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0107NA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
Z0107NA/DG	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 45\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$	-	8	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$; Fig. 4 ; Fig. 5	-	8.5	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.32	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 10\text{ mA}$; T2+ G+	-	50	$\text{A}/\mu\text{s}$
		$I_G = 10\text{ mA}$; T2+ G-	-	50	$\text{A}/\mu\text{s}$
		$I_G = 14\text{ mA}$; T2- G+	-	20	$\text{A}/\mu\text{s}$
		$I_G = 10\text{ mA}$; T2- G-	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
P_{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$

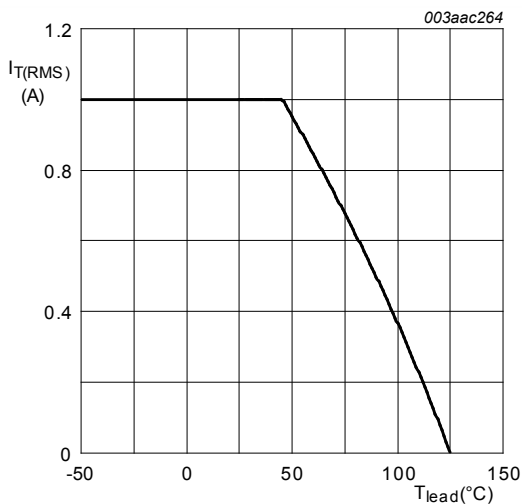
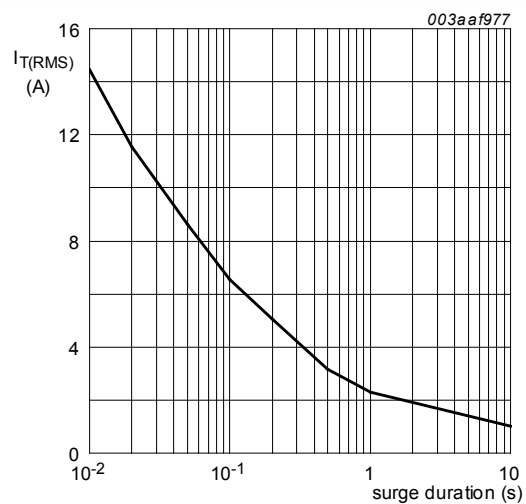


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



$f = 50\text{ Hz}$; $T_{lead} = 45\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

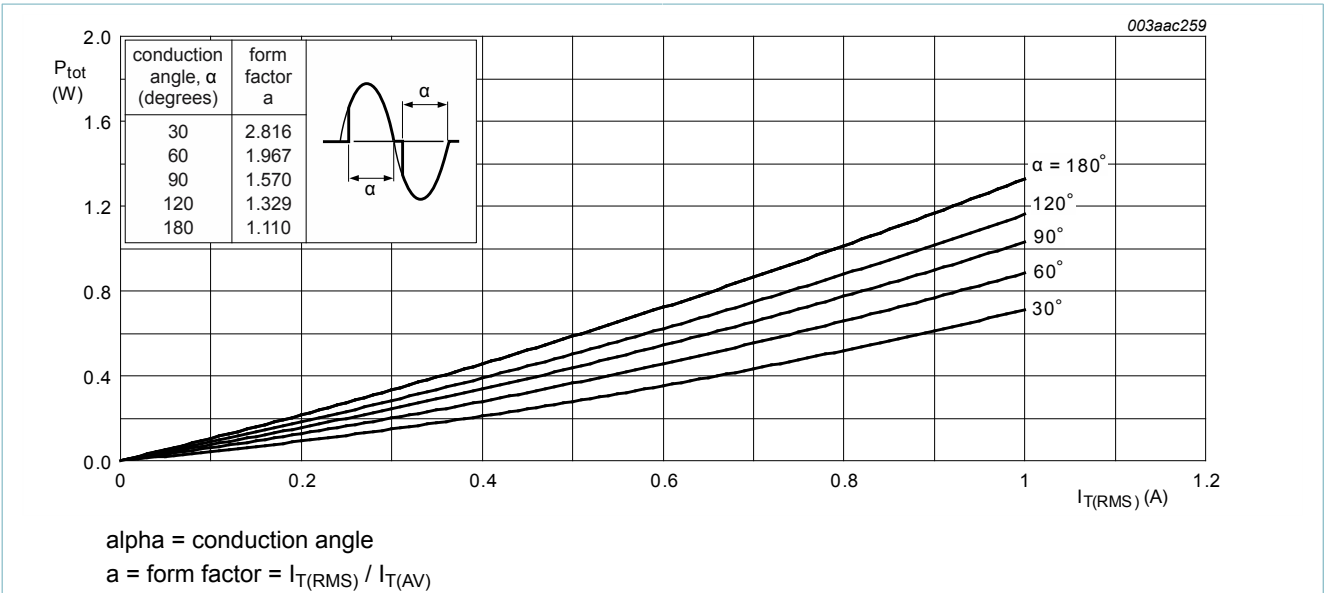


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

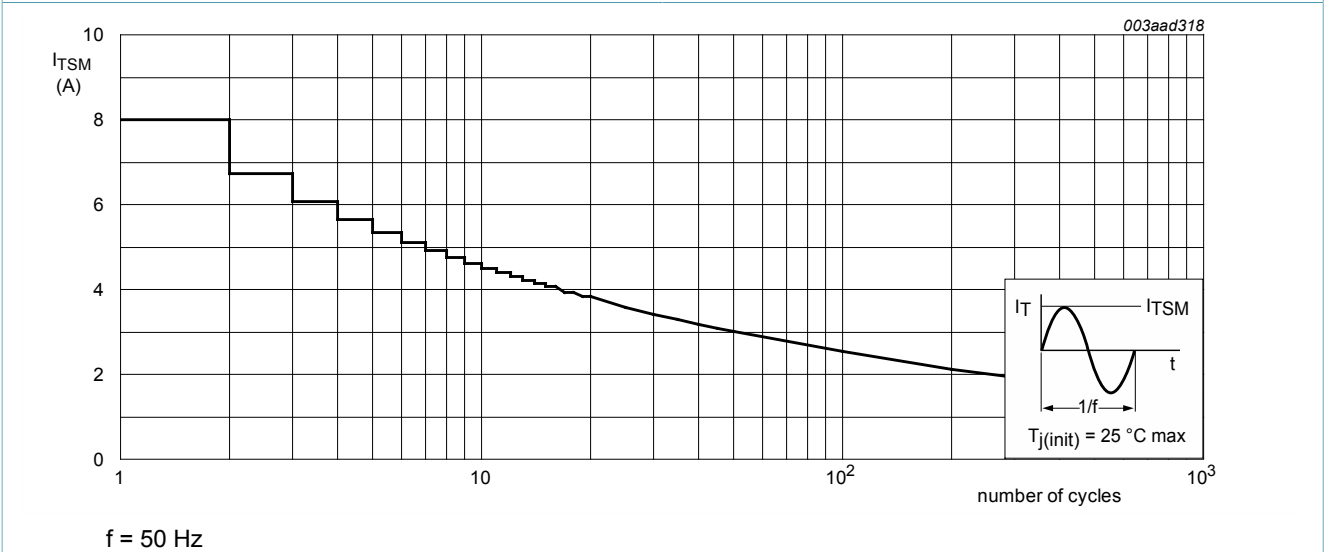
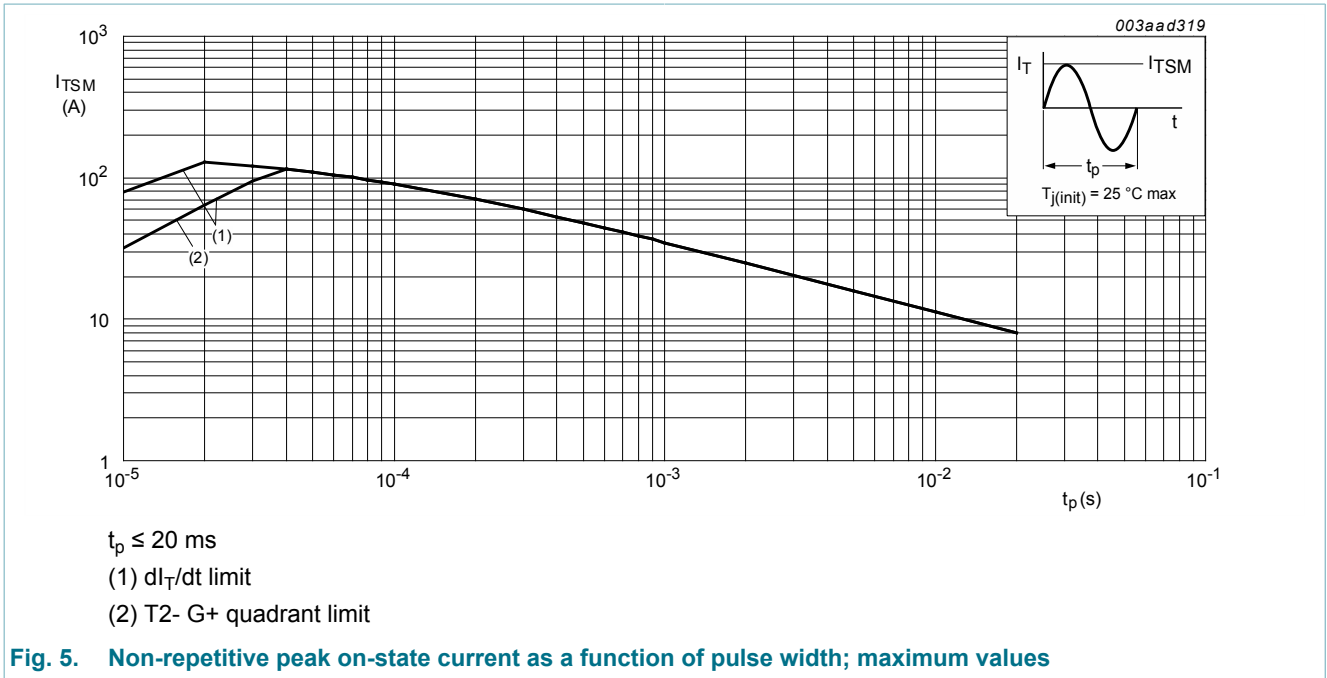


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; printed circuit board; lead length = 4 mm	-	150	-	K/W

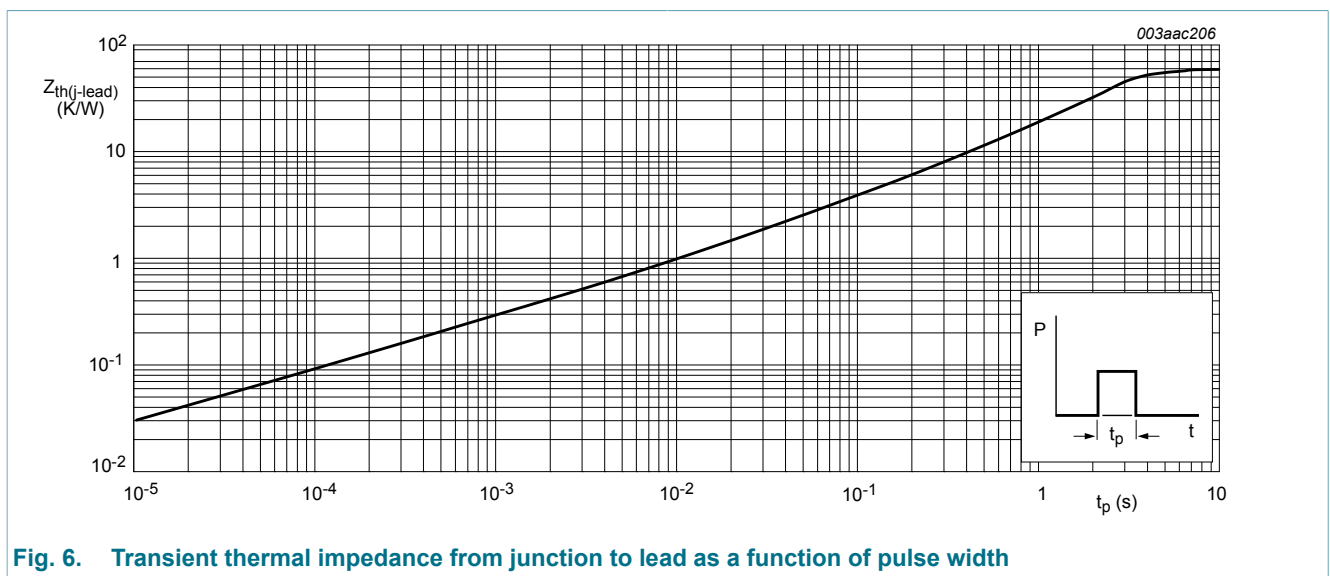
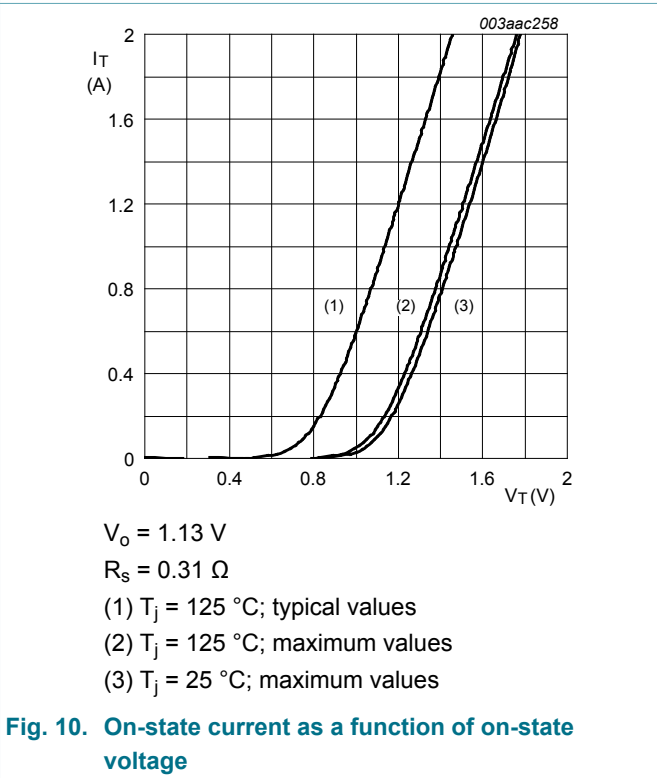
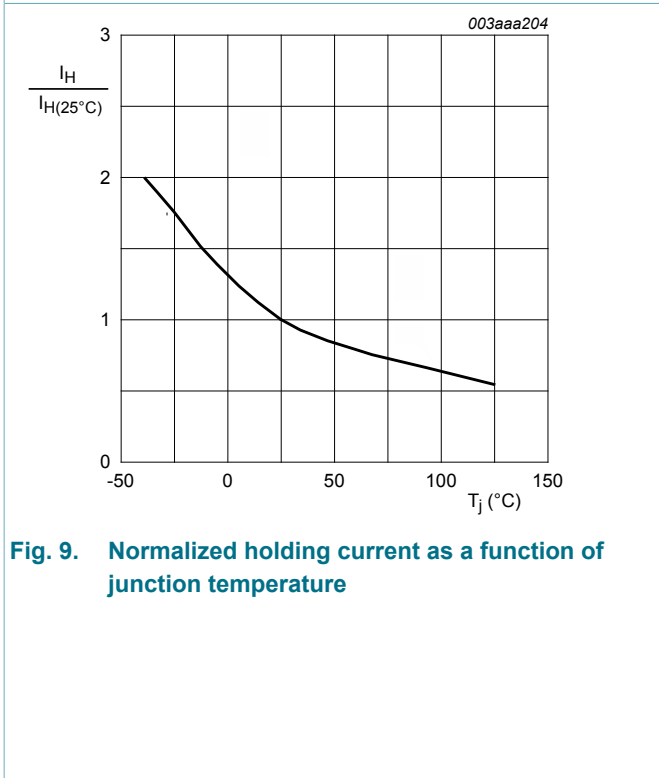
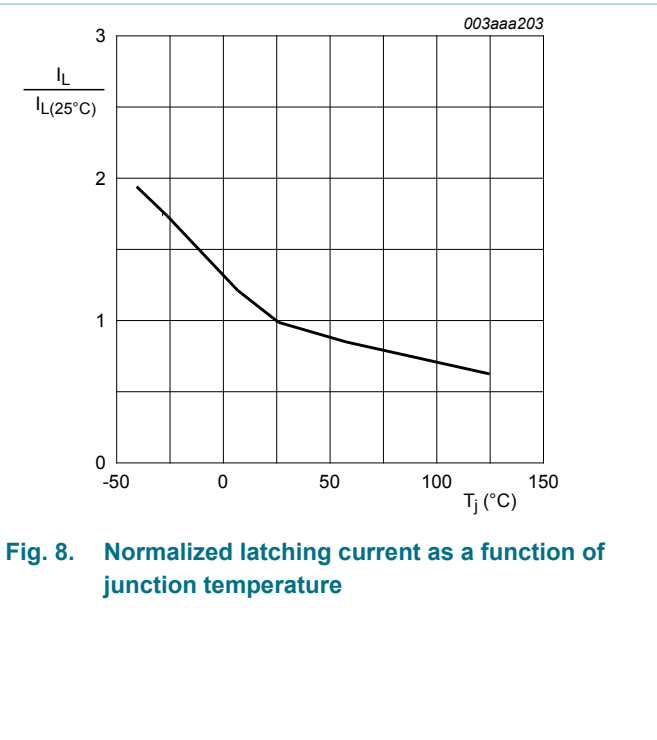
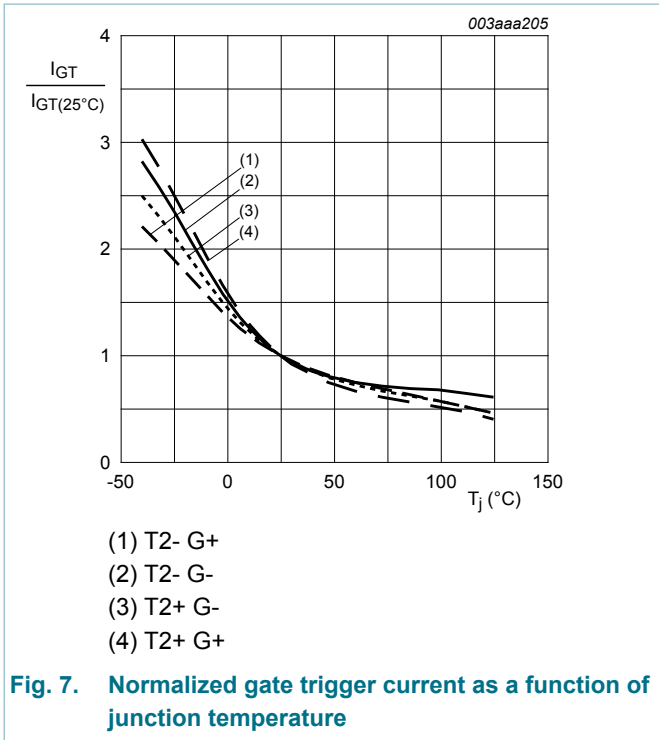


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7	-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7	-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7	-	-	7	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8	-	-	20	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8	-	-	10	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8	-	-	10	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9	-	-	10	mA
V _T	on-state voltage	I _T = 1 A; T _j = 25 °C; Fig. 10	-	1.3	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	-	1	V
		V _D = 800 V; I _T = 0.1 A; T _j = 125 °C	0.2	-	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 110 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 12	20	-	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	V _D = 400 V; T _j = 110 °C; dI _{com} /dt = 0.44 A/ms; I _T = 1 A; gate open circuit	1	-	-	V/μs



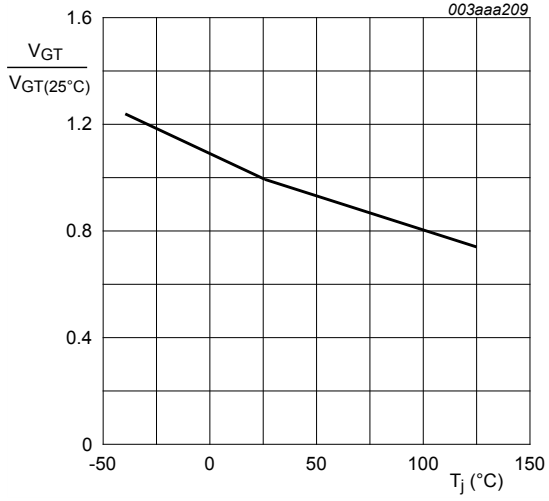


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

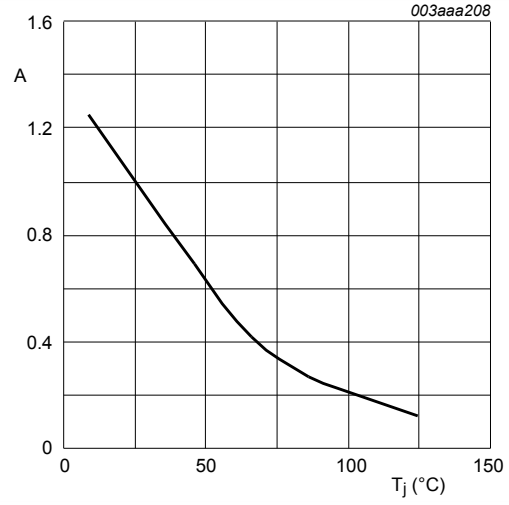


Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{dV_{D(T_j \text{ } ^\circ\text{C})} / dt}{dV_{D(25 \text{ } ^\circ\text{C})} / dt}$$

10. Package outline

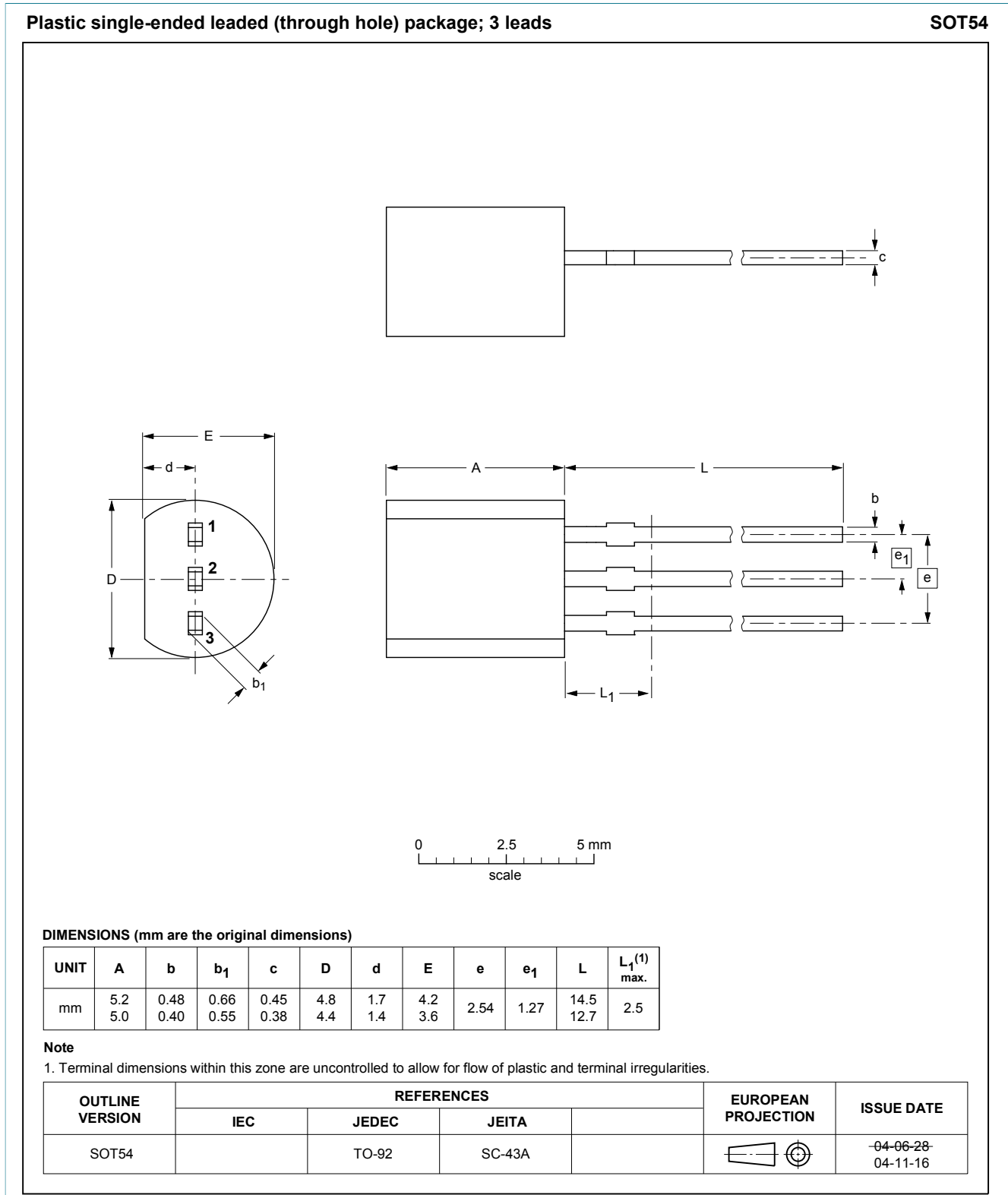


Fig. 13. Package outline TO-92 (SOT54)

11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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